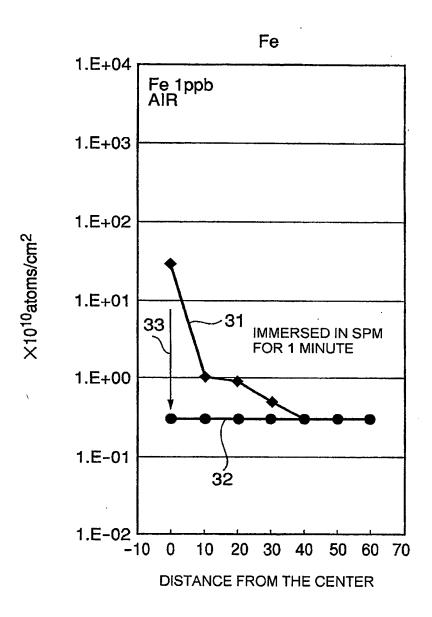


FIG. 3



AND METHOD FOR CLEANING SILICON
CARBIDE PRODUCT
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FIG. 4

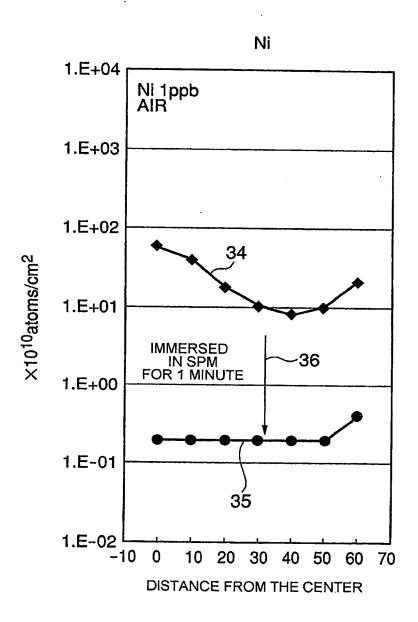
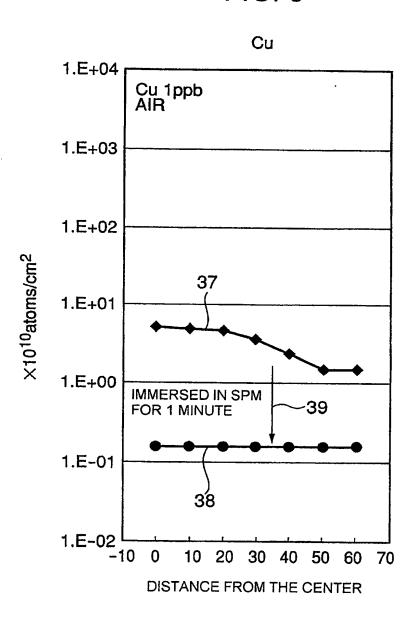


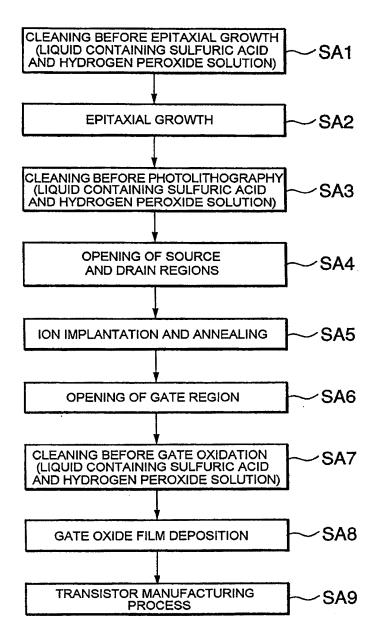
FIG. 5



2  $\overline{S}$ IMPURITY AMOUNTS BEFORE AND AFTER CLEANING SULFURIC ACID + HYDROGEN PEROXIDE SOLUTION 2 **Ni** Element 9  $^{\mathrm{Cmo}}$  метаг імривіту амойит ( $\times 10^{10}$  atoms/cm²)

METHOD FOR PRODUCING THE SAME, AND METHOD FOR CLEANING SILICON CARBIDE PRODUCT Inventor(s): Tadahiro OHMI, et al. DOCKET NO.: 039262-0147

FIG. 7



MEI nOD FOR PRODUCING THE SAME, AND METHOD FOR CLEANING SILICON **CARBIDE PRODUCT** Inventor(s): Tadahiro OHMI, et al. DOCKET NO.: 039262-0147

FIG. 8

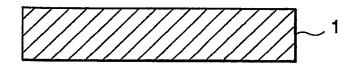


FIG. 9

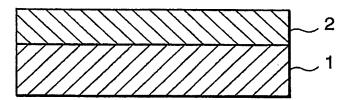


FIG. 10

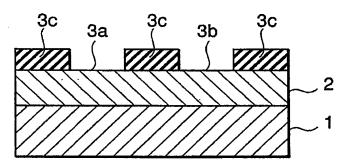
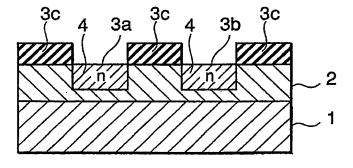


FIG. 11

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MEIROD FOR CLEANING SILICON CARBIDE PRODUCT

FIG. 12

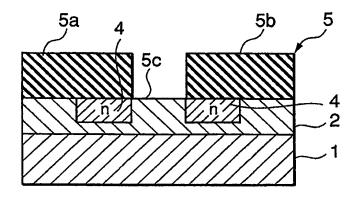


FIG. 13

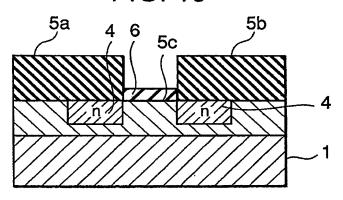


FIG. 14

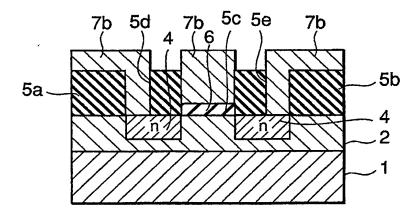
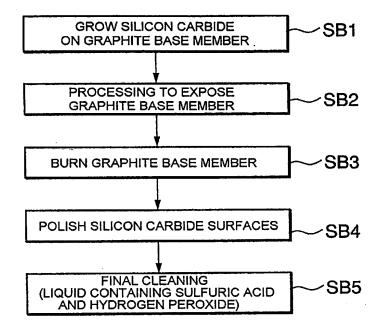


FIG. 15



METHOD FOR PRODUCING THE SAME, AND METHOD FOR CLEANING SILICON CARBIDE PRODUCT

FIG. 16

FIG. 17

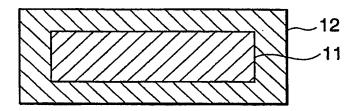


FIG. 18

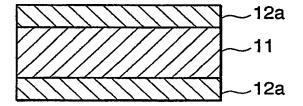


FIG. 19

